

•General Description

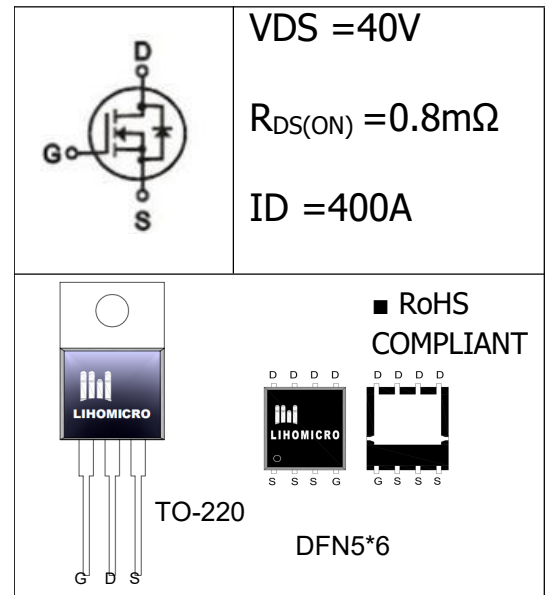
The SGT MOSFET LH008N04G has the low $R_{DS(on)}$, low gate charge, fast switching and excellent avalanche characteristics. This device is suitable for fast charge and lighting.

•Features

- Fast switching
- Low $R_{DS(on)}$ & FOM
- Low Gate Charge

•Application

- LED/LCD/PDP TV and monitor Lighting
- Power Supplies
- DC/DC Converters


•Ordering Information:

Part Number	LH008N04G	LH008N04G
Package	TO-220	DFN5*6
Basic Ordering Unit (pcs)	1000	5000
Normal Package Material Ordering Code	LH008N04GT-TO220-TU	LH008N04GN-DFN5*6-TAP
Halogen Free Ordering Code	LH008N04GT-TO220-TU-HF	LH008N04GN-DFN5*6-TAP -HF

•Absolute Maximum Ratings (TC =25°C)

PARAMETER	SYMBOL	Value	UNIT
Drain-Source Breakdown Voltage	BV_{DSS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current , $T_C = 25^\circ C$	I_D	400	A
Pulsed drain current (TC = 25°C, tp limited by Tjmax) ¹	I_D pulse	1600	A
Single Pulse Avalanche Energy ²	E_{AS}	1300	mJ
Power Dissipation(TC=25°C)	P_D	300	W
Operating Temperature	T_J	-55~+175	°C
Storage Temperature	T_{STG}	-55~+175	°C

●Electronic Characteristics

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	40	--	--	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.6	3.0	V
Drain-source On Resistance ³	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 50A$	--	0.8	1.0	mΩ
		$V_{GS} = 4.5V, I_D = 20A$	--	1.1	1.3	
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 32V, V_{GS} = 0V, T_J = 25^\circ C$	--	--	1	μA
		$V_{DS} = 32V, V_{GS} = 0V, T_J = 85^\circ C$	--	--	5	
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20, V_{DS} = 0V$	--	--	±100	nA
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 20V$ $f = 1.0MHz$	--	8296	--	pF
Output Capacitance	C_{oss}		--	3294	--	
Reverse transfer Capacitance	C_{rss}		--	55	--	
Turn -Off Delay Time	$T_d(off)$	$V_{GS} = 10V,$ $I_D = 50.0A$ $R_G = 4.5\Omega$	--	153	--	ns
Turn-on delay time	$T_d(on)$		--	19	--	
Rise time	T_r		--	84	--	
Fall time	T_f		--	126	--	
Total Gate Charge	Q_g	$I_D = 20A,$ $V_{DS} = 20V$ $V_{GS} = 50V$	--	148	---	nC
Gate-to-Source Charge	Q_{gs}		--	26	--	
Gate-to-Drain Charge	Q_{gd}		--	25	---	

●Diode Characteristics

Reverse Recovery Time	T_{RR}	$V_{GS} = 10V, I_D = 50A$ $di/dt = 100A/\mu S$	--	97	--	nS
Reverse Recovery Charge	Q_{RR}		--	162	--	nC
Diode Forward Voltage	V_{SD}	$T_J = 25^\circ C, I_S = 50A$ $V_{GS} = 0V$	--	1.1	1.3	V

Notes:

- 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
2. $I_{AS} = 40A, V_{DD} = 25V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ C$
3. Pulse Test : Pulse width $\leq 300\mu s, \text{Duty cycle } \leq 2\%$

● **Typical Characteristics**

Fig.1 Typical Output Characteristics

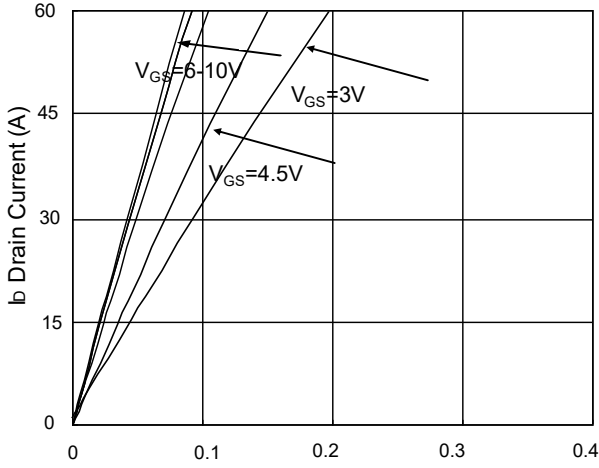


Fig.2 On-Resistance vs G-S Voltage

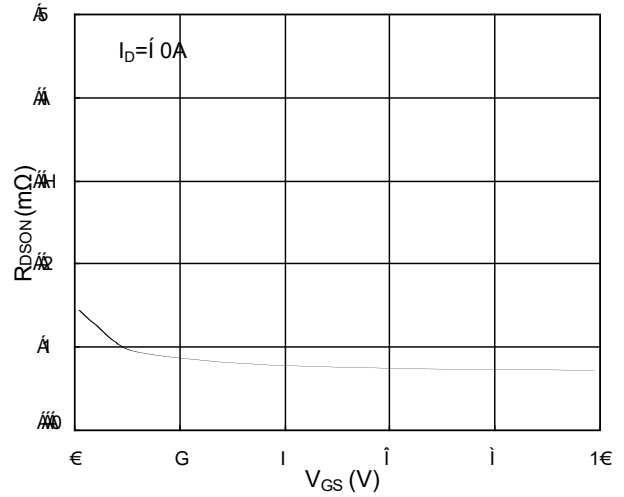


Fig.3 Source Drain Forward Characteristics

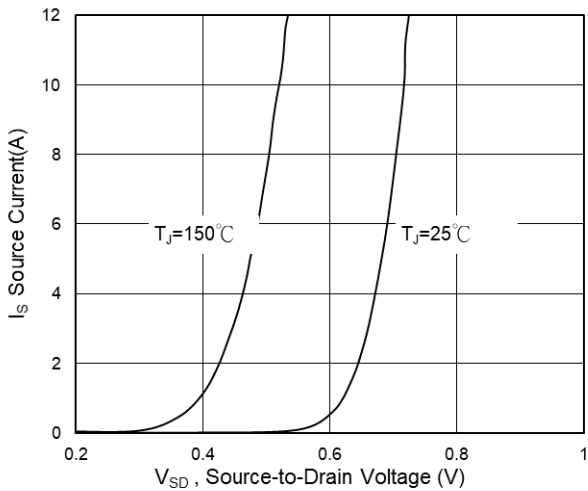


Fig.4 Capacitance

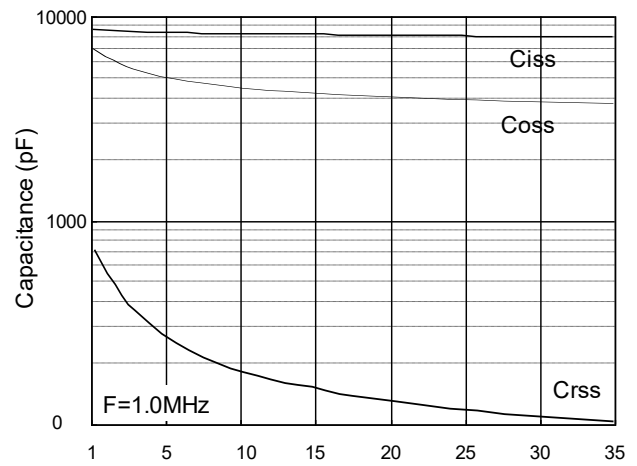


Fig.5 Normalized $V_{GS(th)}$ vs T_J

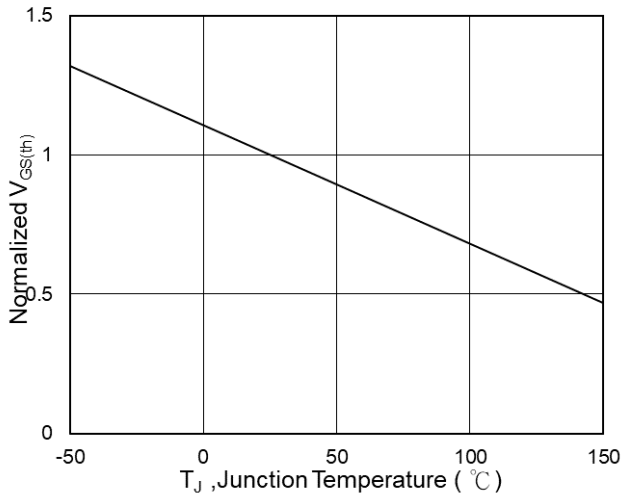
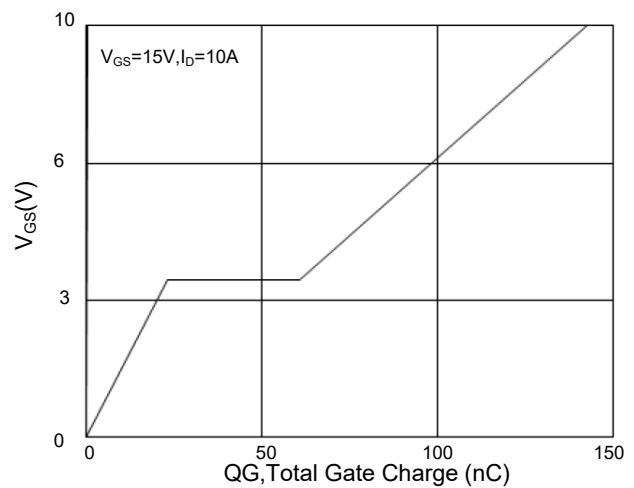


Fig.6 Gate-Charge Characteristics



•Typical Characteristics(cont.)

Fig.7 Normalized R_{DS(on)} vs T_J

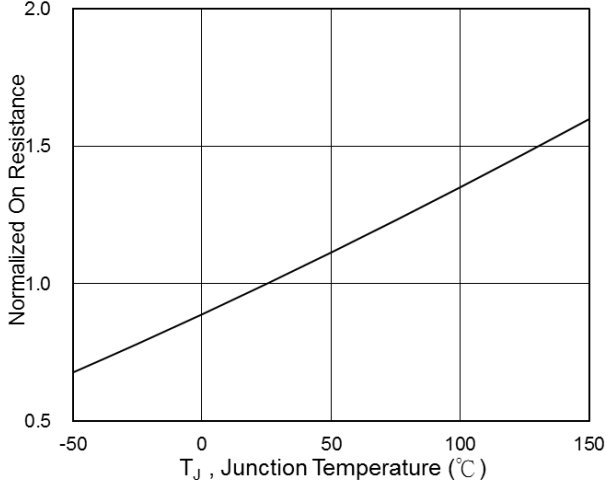


Fig.8 Safe Operating Area

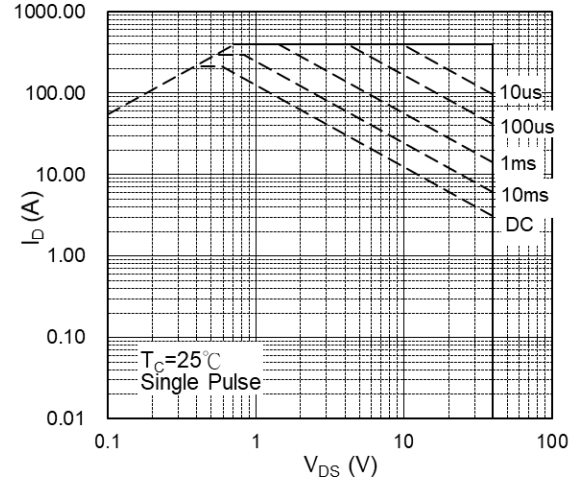
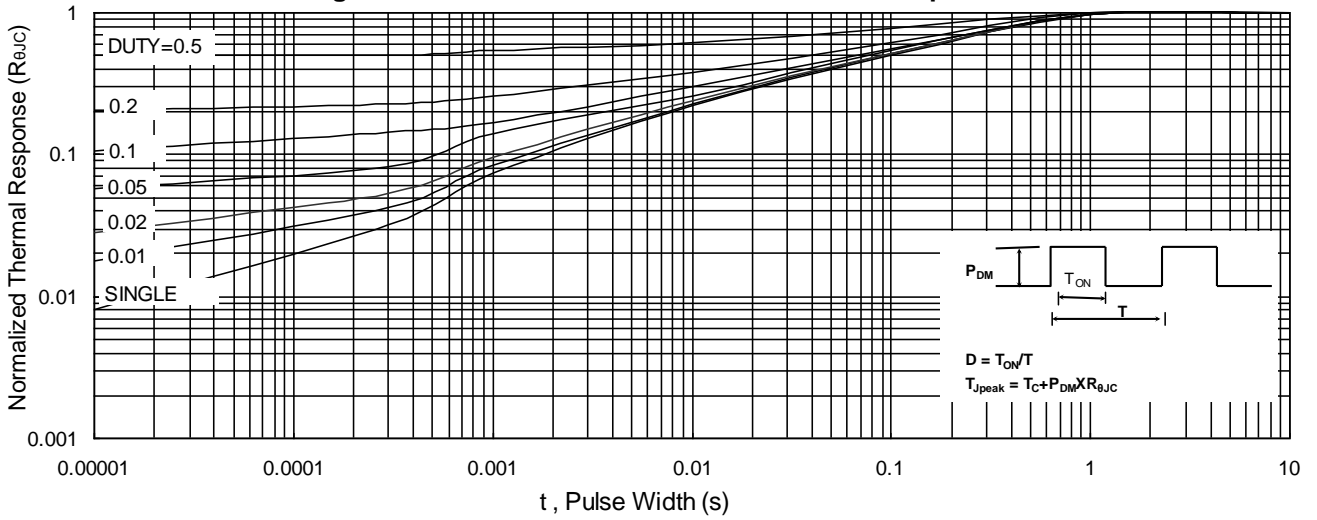


Fig.9 Normalized Maximum Transient Thermal Impedance



• Test Circuits & Waveforms

Fig1.EAS test Circuits

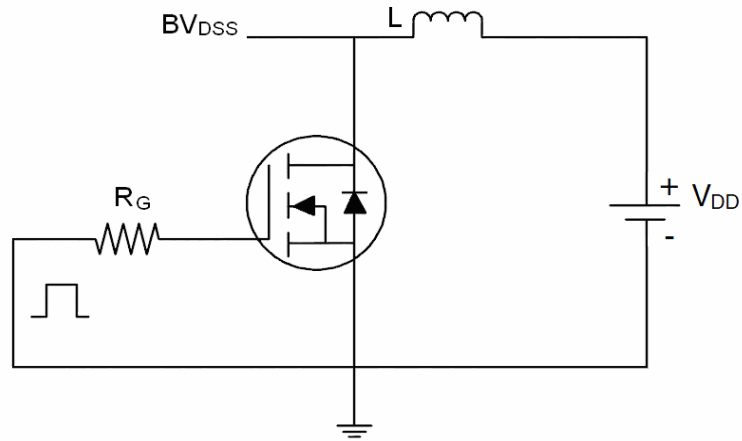


Fig2.Gate charge test Circuit

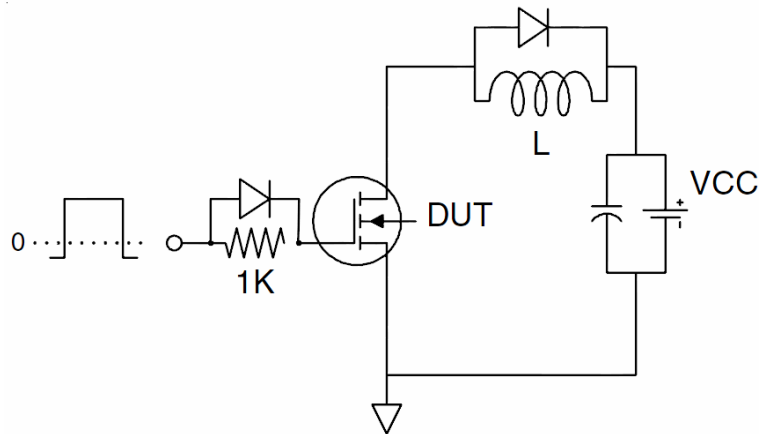
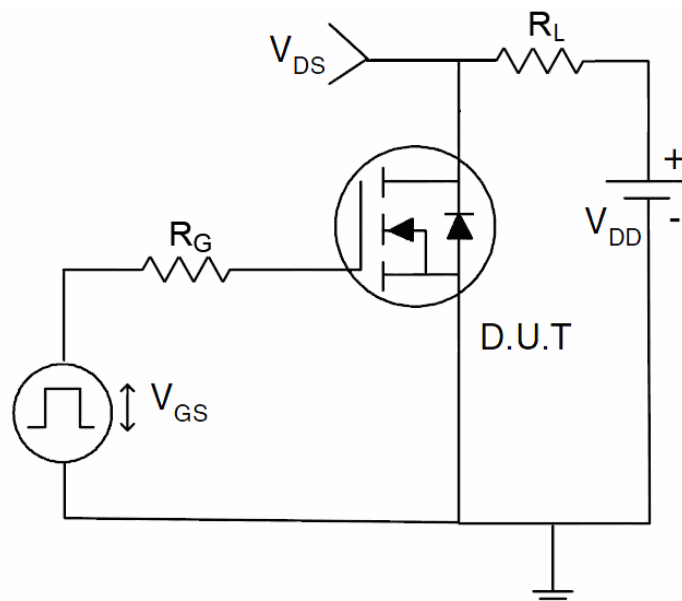


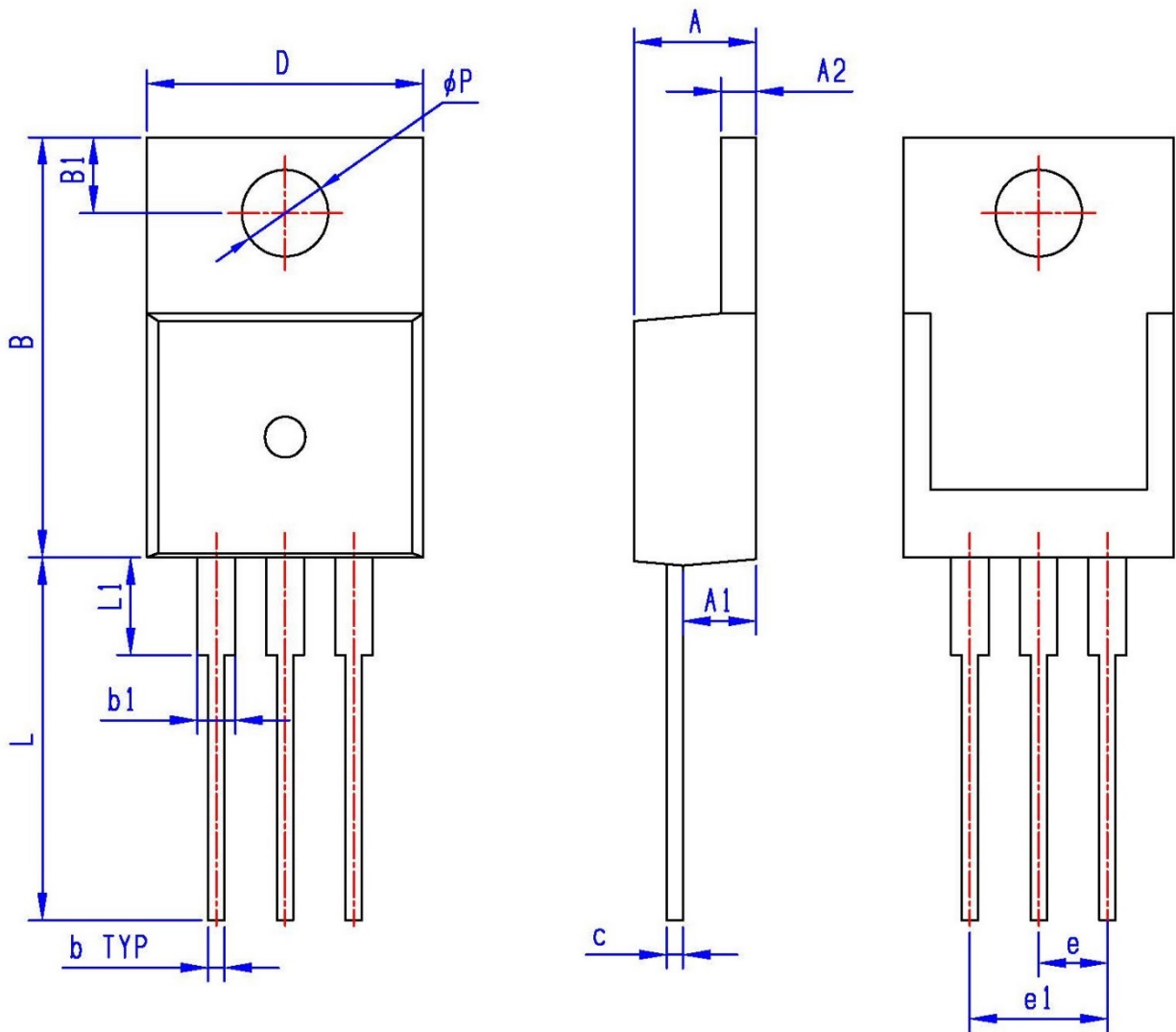
Fig3.Switch Time Test Circuit



•Dimensions (TO-220)

UNIT:mm
UNIT:mm

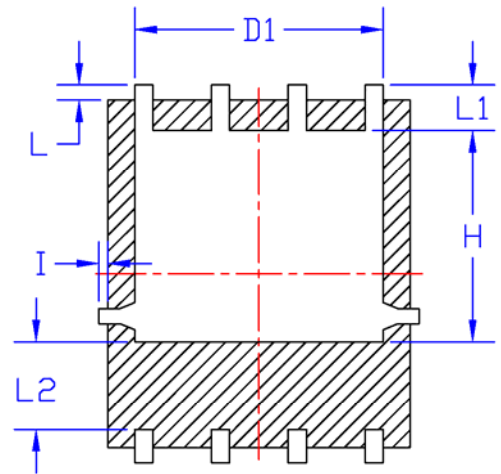
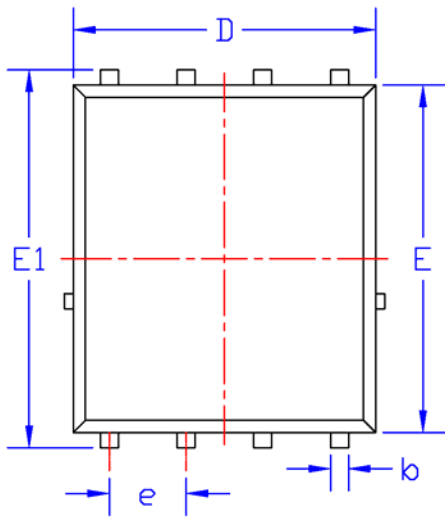
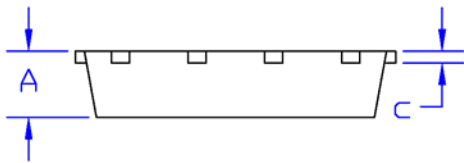
SYMBOL	min	max	SYMBOL	min	max
A	4.25	4.85	B1	2.60	3.00
A1	2.30	3.00	e	2.40	2.70
A2	1.20	1.40	e1	4.95	5.25
b	0.60	0.90	L	12.60	14.40
b1	1.10	1.70	L1	2.40	4.00
c	0.40	0.70	∅P	3.50	3.90
D	9.80	10.60			
B	15.20	16.20			



●Dimensions (DFN5*6)

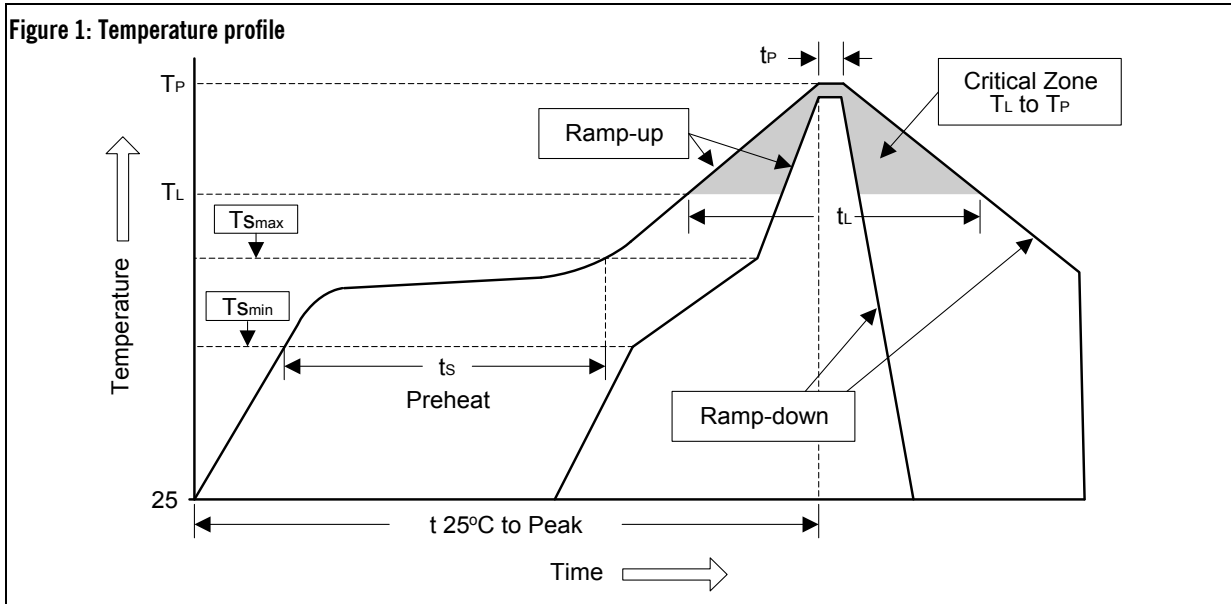
UNIT:mm

SYMBOL	min	max	SYMBOL	min	max
A	1.00	1.20	e	1.27BSC	
b	0.30	0.50	L	0.05	0.30
c	0.20	0.30	L1	0.40	0.80
D	4.80	5.20	L2	1.20	2.00
D1	3.90	4.30	H	3.30	3.80
E	5.50	5.90	I	-	0.18
E1	5.90	6.40			



• Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	< 3°C/sec	< 3°C/sec
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60 to 120 sec	60 to 180 sec
T_{Smax} to T_L		
- Ramp-up Rate	< 3°C/sec	< 3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	< 6°C/sec	< 6°C/sec
Time 25°C to Peak Temperature	< 6 minutes	< 8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec